

25V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate 1kV
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

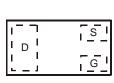
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)



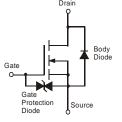












Equivalent Circuit

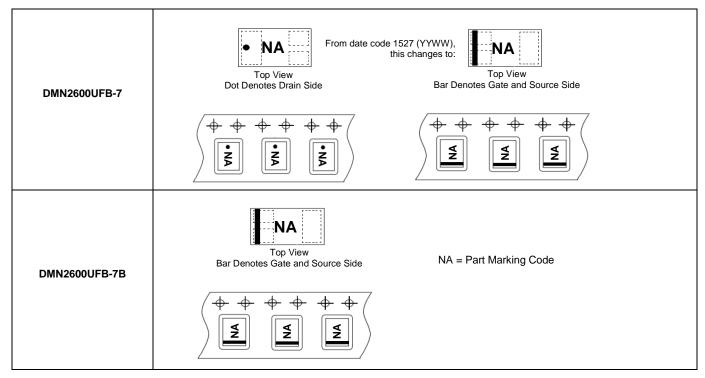
Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2600UFB-7	NA	7	8	3000
DMN2600UFB-7B	NA	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	25	V
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 4)	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	1.3 0.9	Α
Pulsed Drain Current			I _{DM}	3.0	А

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	0.54	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	R _{0JA}	234	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

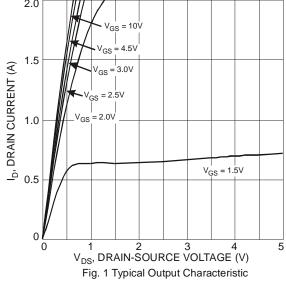
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	25	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1	μΑ	$V_{DS} = 25V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.45	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
				350		$V_{GS} = 4.5V, I_D = 200mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	-	450	mΩ	$V_{GS} = 2.5V, I_D = 100mA$	
				600		$V_{GS} = 1.8V, I_D = 75mA$	
Forward Transfer Admittance	Y _{fs}	40	-	-	mS	$V_{DS} = 3V, I_D = 200mA$	
Diode Forward Voltage	V_{SD}	-	-	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	70.13	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	7.56	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	5.59	-	pF	1 = 1.000112	
Gate Resistance	Rg	-	72.3	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	-	0.85	-	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_gs	-	0.16	-	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$	
Gate-Drain Charge	Q_{gd}	-	0.11	-	nC	$I_D = 1A$	
Turn-On Delay Time	t _{D(on)}	-	4.1	-	ns		
Turn-On Rise Time	t _r	-	11.5	-	ns	$V_{DS} = 15V, R_{L}=15\Omega$	
Turn-Off Delay Time	t _{D(off)}	-	34.8	-	ns	$V_{GS} = 10V, R_G = 6\Omega$	
Turn-Off Fall Time	t _f	-	20.9	-	ns		

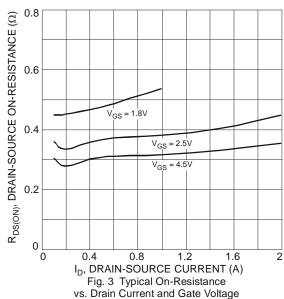
Notes:

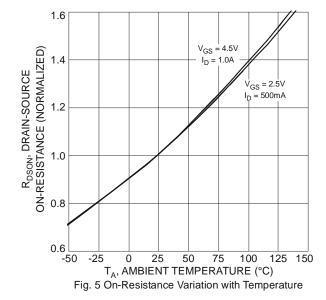
- 4. Device mounted on FR-4 substrate PCB board, with minimum recommended pad layout.
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to production testing.



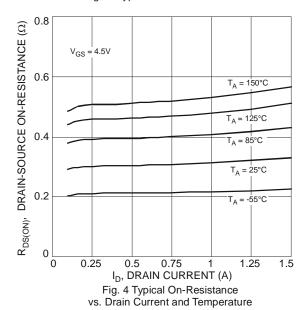








1.5 V_{DS} = 5V V_{DS} = 5V 1.0 V_{DS} = 5V T_A = 150°C T_A = 25°C T_A = 35°C T_A = 25°C T_A = 25°C T_A = 25°C



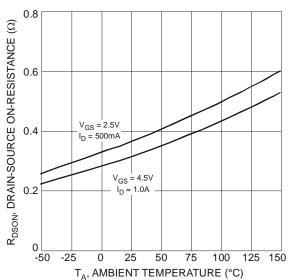


Fig. 6 On-Resistance Variation with Temperature

DMN2600UFB



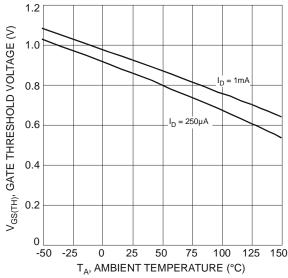
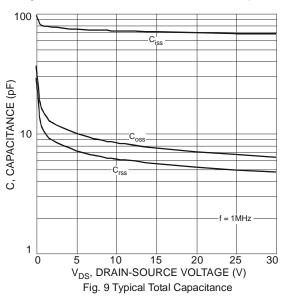
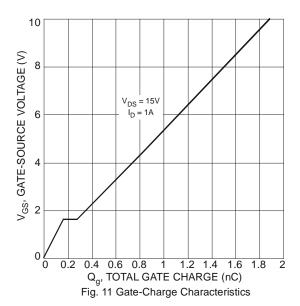
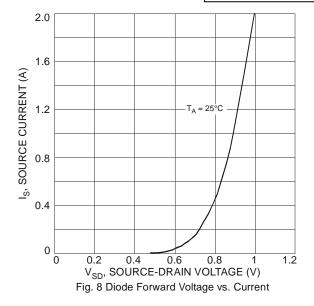
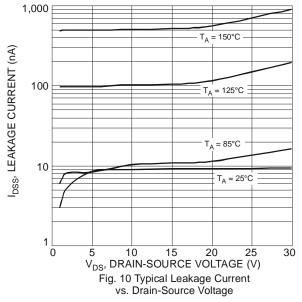


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

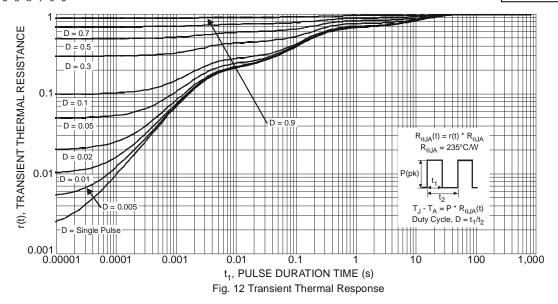






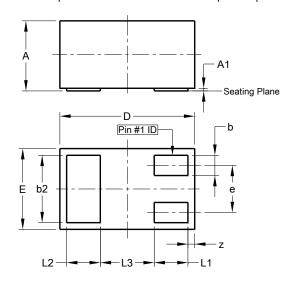






Package Outline Dimensions

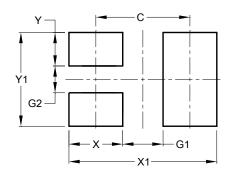
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	ı	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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